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Customer No.: 31561
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IN THE SPECIFICATION

#68 Audt

Please amend the specification as follows.

M. Brunson

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[0012] Also to attain the foregoing and other aspects, the present invention proposes a process for fabricating a chip with bumps comprising the following steps. First providing a chip that has an active surface and at least a bonding pad, wherein the bonding pad exposes the active surface. Then performing an activation step, depositing a medium layer on the bonding pad. Forming at least a bump body on the medium layer in an ~~electricless~~ electroless plating way, and forming a bump body passivation layer covering the bump body except for a portion of the bump body that connects to the medium layer.

B1

[0013] According to a preferred embodiment of the present invention, the material of the bump body is nickel, and the material of the bump body passivation layer is gold. The height of the bump body is about 5 to 10 microns, and the height of the bump body passivation layer is about 1 to 3 microns. The bump body and the bump body passivation layer are formed by ~~electricless~~ electroless plating.

[0018] A bumping process which includes steps of producing a bump body and a bump body passivation layer follows. In the step of producing a bump body, at least a bump body 220 is formed by ~~electricless~~ electroless plating to be electrically connected to the bonding pad 216. It is accomplished by following steps. First, an activation step is performed. During the activation step, the chip 210 is dipped into a zinc ions containing solution, then zinc is deposited on the bonding pad 216 of the chip 210 to form a medium layer 228, wherein a material of the medium layer includes zinc. Since zinc is utilized to be an activator before the following ~~electricless~~ electroless plating, the deposition

B2